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Kindly rewrite the paragraph appearing at page 5, lines 6-7, to read as follows:

A₂ Figs. 1(A) through 1(E) show process steps of an embodiment of a selective oxidation method according to the present invention.

In the Claims²

Kindly amend Claim 1 to read as follows:

1. (Amended) A method for selectively oxidizing a silicon wafer, said method comprising:

A₃ covering each of whole areas of both surfaces of a silicon wafer with an oxidation inhibitor film with interposition of a pad oxide film;

patterning said pad oxide film and an oxidation inhibitor film on said pad oxide film on one surface of said wafer to form desired patterns to partially expose the one surface of said wafer through said patterns;

✓ removing said pad oxide film and said oxidation inhibitor film on said pad oxide film formed on the other surface of said wafer to expose the whole area of the other surface of said wafer;

² A copy of any revised claims showing additions and deletions thereto is attached as ATTACHMENT "B".